PATENT COOPERATION TREATY

From the INTERNATIONAL SEARCHING AUTHORITY			
To: SEMICONDUCTOR ENERGY LABORATORY CO., LTD. 398, Hase, Atsugi-shi, Kanagawa 2430036 Japan	INTERNAT Date of mailing (day/month/year)	PCT RITTEN OPINION OF RONAL SEARCHING (PCT Rule 43bis.1)	AUTHORITY
Applicant's or agent's file reference 00000PCT7465	FOR FURTHER A	See paragraph 2 below	
International application No. International filing date	<u> Language</u>	Priority date (day/month	lyear)
PCT/JP2004/016183 25.10	.2004	28.10	2003
International Patent Classification (IPC) or both national classific Int.Cl ⁷ H01L 29/786, H01L 21/336, H01L 21/766 Applicant SEMICONDUCTOR ENERGY LABOR	8, HO1L 21/288,		2F 1/1368
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1. This opinion contains indications relating to the following ite Box No. I Basis of the opinion Box No. II Priority Box No. III Non-establishment of opinion with reg Box No. IV Lack of unity of invention Box No. V Reasoned statement under Rule 43bis.1(citations and explanations supporting s	ard to novelty, inventi a)(i) with regard to nov		
Box No. VI Certain documents cited			
Box No. VII Certain defects in the international app Box No. VIII Certain observations on the internation			
2. FURTHER ACTION		•	
If a demand for international preliminary examination is ma International Preliminary Examining Authority ("IPEA") excel other than this one to be the IPEA and the chosen IPEA has n opinions of this International Searching Authority will not b If this opinion is, as provided above, considered to be a written	pt that this does not ap otified the Internation e so considered. opinion of the IPEA, t	oly where the applicant chall Bureau under Rule 66.1 The applicant is invited to the applicant i	nooses an Authority bis(b) that written submit to the IPEA
a written reply together, where appropriate, with amendments, PCT/ISA/220 or before the expiration of 22 months from the properties of the			of mailing of Form
For further options, see Form PCT/ISA/220.		•	
3. For further details, see notes to Form PCT/ISA/220.			
Name and mailing address of the ISA/JP	Authorized officer		4M 3123
Japan Patent Office	Sonoko	Miyazaki	4M 3123
3-4-3 Kasumigaseki Chivoda-ku Tokyo 100-8015 Japan		_	3462

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2004/016183

Bo	x No. I	Basis of the o	pinion								
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WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No. PCT/JP2004/ 016183

Box No. V	Reasoned statement under Rule 43bis.1(a)(i) with regard to novelty, inventive s citations and explanations supporting such statement	tep or industrial applicability;
1 Statemen		

Statement		9	· · · · · · · · · · · · · · · · · · ·	
Novelty (N)	Claims	3-4,7,9,11-14		
	Claims	1-2,5-6,8,10		
Inventive step (IS)	Claims	12		
	Claims	1-11,13-14		
Industrial applicability (IA	1) Claims	1-14		

2. Citations and explanations

D1:JP 2003-98548 A(HITACHI, LTD.,)

2003.04.03, whole document, Figs. 1-7

D2:JP 2002-49333 A(SEMICONDUCTOR ENERGY LABORATORY CO., LTD.)

2002.02.15, whole document, Figs.1-21

D3:JP 2003-506886 A(PATTERNING TECHNOLOGY LIMITED)

Claims

2003.02.18, whole document, Figs.1-27

D4:WO 1997/043689 A1(SEIKO EPSON CORPORATION)

1997.11.20,page27-28, Figs.14-16

D5:JP 7-297404 A(KABUSHIKI KAISHA TOSHIBA)

1995.11.10, whole document, Figs. 1-6

D6:JP 4-56168 A(STANLEY ELECTRIC CO., LTD.)

1992.02.24, whole document, Fig.1

[Claims 1-2,5-6,8,10]

The subject matter of claims 1-2,5-6,8,10 does not appear to be novel and to involve an inventive step with respect to the cited document D1.

The subject matter of claims 1-2,5-6,8,10 is disclosed in the cited document D1.

[Claims 3-4,7,9]

The subject matter of claims 3-4,7,9 does not appear to involve an inventive step in view of the cited documents D1- D2.

D2 discloses that a driver circuit is constructed by a second thin film transistor which comprises the same layer structure of a first thin film transistor and the driver circuit comprises only n-channel type thin film transistor.

[Claims 11]

The subject matter of claim 11 does not appear to involve an inventive step in view of the cited documents D1- D4.

D3-D4 disclose a mask is formed by a droplet discharge method.

[Claims 12]

The subject matter of claim 12 is neither disclosed in any of the documents cited in the ISR nor obvious to a person skilled in the art.

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International application No. PCT/JP2004/016183

Supplemental Box

In case the space in any of the preceding boxes is not sufficient. Continuation of: Box $No\cdot V$

[Claims 13]

The subject matter of claim 13 does not appear to involve an inventive step in view of the cited documents D1- D5.

D5 discloses the step of laminating a gate insulating layer, a semiconductor layer, and an insulating layer over the gate electrode is carried out without exposing to the atmosphere.

[Claims 14]

The subject matter of claim 14 does not appear to involve an inventive step in view of the cited documents D1- D6.

D6 discloses the gate insulating film is sequentially laminated by a first silicon nitride film, a silicon oxide film, and a second silicon nitride film.